

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-14. (Canceled)

15. (Currently Amended) ~~A polishing pad used for~~method for polishing a circular substrate having a predetermined cross-sectional area with a polishing pad, the polishing pad comprising a center and a polishing surface upon which ~~polishing a particular substrate having a known cross-sectional area~~V-shaped or U-shaped grooves having a radial pattern are formed, the method comprising:

disposing the substrate laterally outward from the center of the polishing pad with a portion of the polishing pad surface provided immediately below the substrate; and
polishing the substrate using the polishing pad,

~~wherein grooves having a radial pattern are formed on a surface of the polishing pad, and an average value of the total volumes of all the groove parts~~grooves existing in the portion of the polishing pad surface immediately below the substrate in the grooves (an average value of the sum totals of the groove volumes in parts immediately below the substrate) is 0.06 to 0.23 when represented by the average value of the sum totals of the total groove volumes in parts immediately below the substratethe polishing pad portion (mm³) / area of the substrate (mm²).

16. (Canceled)

17. (Currently Amended) ~~The polishing pad~~method according to Claim 15, wherein the grooves have a constant groove width and are formed so that angles between the grooves are more than the values obtained by the mathematical formula 1 as follows:

(Mathematical formula 1)

An an angle between the grooves = $2 \times \sin^{-1}$ (a width of the grooves / (2 x (a distance from the center of the polishing pad to the center of the substrate – a radius of the substrate))).

18. (Canceled)

19. (Currently Amended) The ~~polishing pad~~method according to Claim 15, wherein the grooves have groove widths of 2.0 mm or less.

20. (Canceled)

21. (Currently Amended) The ~~polishing pad~~method according to Claim 15, wherein the polishing pad is a nonwoven type or a suede type.

22-24. (Canceled)

25. (Currently Amended) The method for ~~producing~~polishing a substrate according to Claim ~~23~~15, wherein as the substrate to be polished, a silicon single crystal wafer or an SOI wafer is used.

26. (Canceled)

27. (Currently Amended) A method for processing a circular polishing pad having a center and a surface, the pad being used for polishing a circular substrate having a known cross-sectional area, the method comprising ~~which is a method for forming V-shaped or U-shaped grooves on a~~ the surface of a ~~the polishing pad used for polishing a particular substrate having a known cross-sectional area, comprising forming the grooves so as to have a radial pattern, and at this time forming the grooves so that~~ during use when at least a portion of the circular polishing pad is located immediately below the circular substrate, an average value of the total volumes of all the groove parts ~~grooves in the polishing pad surface portion existing immediately below the substrate in the grooves (an average value of the sum totals of the groove volumes in parts immediately below the substrate)~~ complies with a relation of 0.06 to 0.23 when represented by the average value of the total groove volumes in the polishing pad

~~portions~~sum totals of the groove volumes in parts immediately below the substrate (mm^3) /
area of the substrate (mm^2).

28. (Canceled)

29. (Previously Presented) The method for processing a polishing pad according to Claim 27, wherein the grooves are formed so that angles between the grooves are more than values obtained by the mathematical formula 1 as follows:

(Mathematical formula 1)

An angle between the grooves = $2 \times \sin^{-1}$ (a width of the grooves / (2 x (a distance from the center of the polishing pad to the center of the substrate – a radius of the substrate))).

30. (Canceled)

31. (Previously Presented) The method for processing a polishing pad according to Claim 27, wherein the grooves are formed so as to have groove widths of 2.0 mm or less.

32. (Canceled)

33. (Previously Presented) The method for processing a polishing pad according to Claim 27, wherein the polishing pad is a nonwoven type or a suede type.

34. (Canceled)

35. (Currently Amended) A method for ~~producing~~polishing a substrate, comprising a step of polishing a substrate by using the polishing pad processed by the method according to Claim 27.

36. (Canceled)

37. (Currently Amended) The method for ~~producing~~polishing a substrate according to Claim 35, wherein as the substrate to be polished, a silicon single crystal wafer or an SOI wafer is used.

38. (Canceled)